PROCESS CP245

Power Transistor

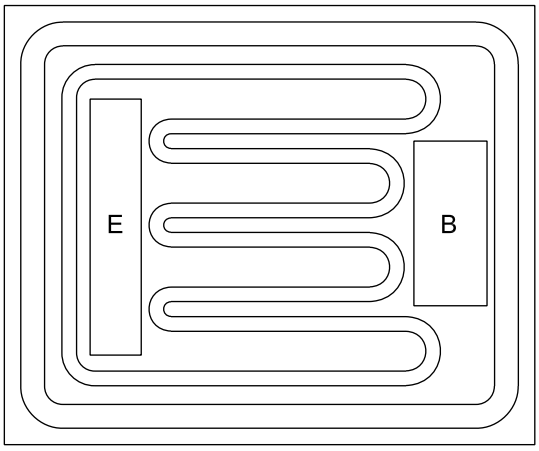
NPN, 8.0A Power Transistor Chip

Central™ Semiconductor Corp.

PROCESS DETAILS

Process	MULTIEPITAXIAL MESA
Die Size	120 x 145 MILS
Die Thickness	13 MILS
Base Bonding Pad Area	20 x 45 MILS
Emitter Bonding Pad Area	14 x 70 MILS
Top Side Metalization	Al - 50,000Å
Back Side Metalization	Cr / Ni / Ag - 10,000Å

GEOMETRY



BACKSIDE COLLECTOR R0

GROSS DIE PER 4 INCH WAFER

640

PRINCIPAL DEVICE TYPES

MJE15030

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R0 (4- April 2005)